

HIGH-SPEED 3.3V 32K x 16 SYNCHRONOUS DUAL-PORT STATIC RAM

IDT70V9279S/L

Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 9/12/15ns (max.)
- Low-power operation
 - IDT70V9279S Active: 429mW (typ.)
 - Standby: 3.3mW (typ.)

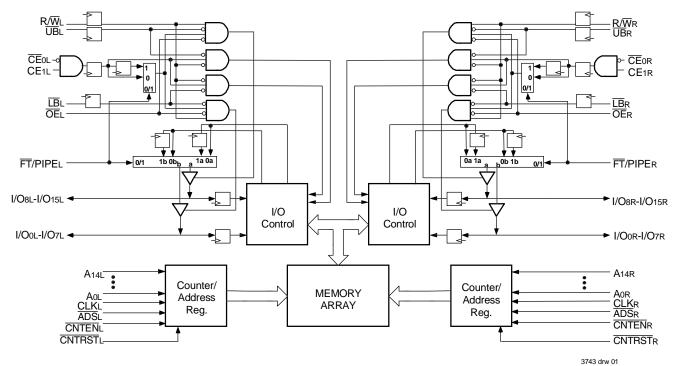
 IDT70V9279L

 Active: 429mW (typ.)

 Standby: 1.32mW (typ.)
- Flow-through or Pipelined output mode on either port via the FT/PIPE pin
- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic

- Full synchronous operation on both ports
 - 4ns setup to clock and 1ns hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 9ns clock to data out in the Pipelined output mode
 - Self-timed write allows fast cycle time
 - 15ns cycle time, 66MHz operation in Pipelined output mode
- Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- LVTTL- compatible, single 3.3V (±0.3V) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 128-pin Thin Quad Flatpack (TQFP) package

Functional Block Diagram



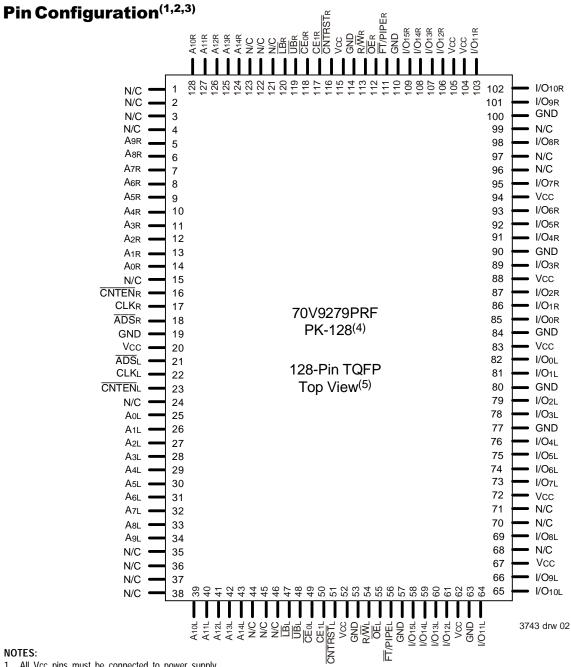
JANUARY 2001

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Description:

The IDT70V9279 is a high-speed 32K x 16 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times.

With an input data register, the IDT70V9279 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{\text{CE}}_0$ and CE₁, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 429mW of power.



- 1. All Vcc pins must be connected to power supply.
- All GND pins must be connected to ground.
- Package body is approximately 14mm x 20mm x 1.4mm.
- This package code is used to reference the package diagram.
- This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names		
CEOL, CE1L	CEOR, CE1R	Chip Enables		
R/\overline{W}_L	R/WR	Read/Write Enable		
ŌĒL	OE R	Output Enable		
A0L - A14L	A0R - A14R	Address		
I/O0L - I/O15L	I/Oor - I/O15R	Data Input/Output		
CLKL	CLKR Clock			
Ū <u>B</u> L	ŪB̄R	Upper Byte Select		
LB L	IB R	Lower Byte Select		
AD S L	AD SR	Address Strobe Enable		
CNTENL	<u>CNTEN</u> R	Counter Enable		
CNTRSTL	<u>CNTRST</u> R	Counter Reset		
FT/PIPEL FT/PIPER		Flow-Through / Pipeline		
V	CC	Power		
G	ND	Ground		

3743 tbl 01

Truth Table I—Read/Write and Enable Control(1,2,3)

ŌĒ	CLK	Œ₀	CE ₁	ŪB	LΒ	R/W	Upper Byte I/O ₈₋₁₅	Lower Byte I/O ₀₋₇	MODE
Х	\uparrow	Н	Х	Χ	Χ	Х	High-Z	High-Z	Deselected-Power Down
Х	\uparrow	Х	L	Х	Χ	Х	High-Z	High-Z	Deselected-Power Down
Х	\uparrow	L	Н	Н	Н	Х	High-Z	High-Z	Both Bytes Deselected
Х	\uparrow	L	Н	L	Н	L	Din	High-Z	Write to Upper Byte Only
Х	\uparrow	L	Н	Н	L	L	High-Z	DATAIN	Write to Lower Byte Only
Х	\uparrow	L	Н	L	L	L	DATAIN	DATAIN	Write to Both Bytes
L	1	L	Н	L	Н	Н	DATA out	High-Z	Read Upper Byte Only
L	1	L	Н	Н	L	Н	High-Z	DATA _{OUT}	Read Lower Byte Only
L	\uparrow	L	Н	L	L	Н	DATA out	DATAout	Read Both Bytes
Н	\uparrow	L	Н	L	L	Х	High-Z	High-Z	Outputs Disabled

NOTES:

"H" = V_{IH}, "L" = V_{IL}, "X" = Don't Care.
 ADS, CNTEN, CNTRST = X.
 OE is an asynchronous input signal.

Truth Table II—Address Counter Control^(1,2)

Address	Previous Address	Addr Used	CLK	ĀDS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
Х	Х	0	1	Х	Х	L	Dvo(0)	Counter Reset to Address 0
An	Х	An	1	L ⁽⁴⁾	Χ	Н	Dvo(n)	External Address Loaded into Counter
An	Ар	Ар	1	Н	Н	Н	Dvo(p)	External Address Blocked—Counter disabled (Ap reused)
Х	Ар	Ap + 1	1	Н	L ⁽⁵⁾	Н	Dvo(p+1)	Counter Enabled—Internal Address generation

NOTES:

3743 tbl 03

- 1. "H" = V_{IH} , "L" = V_{IL} , "X" = Don't Care.
- 2. \overline{CE}_0 , \overline{LB} , \overline{UB} , and \overline{OE} = VIL; CE1 and R/ \overline{W} = VIH.
- 3. Outputs configured in Flow-Through Output mode; if outputs are in Pipelined mode the data out will be delayed by one cycle.
- 4. \overline{ADS} is independent of all other signals including \overline{CE}_0 , \overline{CE}_1 , \overline{UB} and \overline{LB} .
- The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other signals including CE₀, CE₁, UB and LB.

Recommended Operating Temperature and Supply Voltage^(1,2)

Grade	Ambient Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V

3743 tbl 04

NOTES:

- Industrial temperature: for specific speeds, packages and powers contact your sales office.
- 2. This is the parameter Ta. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vcc	Supply Voltage	3.0	3.3	3.6	٧
GND	Ground	0	0	0	٧
V⊪	Input High Voltage	2.2	_	Vcc+0.3V ⁽²⁾	٧
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	V

3743 tbl 05

NOTES:

- 1. $Vil \ge -1.5V$ for pulse width less than 10 ns.
- 2. VTERM must not exceed Vcc +0.3V.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
Іоит	DC Output Current	50	mA

NOTES:

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- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc +0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 0.3V.

Capacitance⁽¹⁾ (TA = +25°C, f = 1.0MHz)

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	$V_{IN} = 3dV$	9	pF
Соит ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF

NOTES

- 1. These parameters are determined by device characterization, but are not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references Ci/o.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 3.3V ± 0.3V)

				279S	70V9		
Symbol	Parameter	Test Conditions	Min.	Мах.	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	$V_{CC} = 3.6V$, $V_{IN} = 0V$ to V_{CC}	_	10	_	5	μΑ
ILO	Output Leakage Current	\overline{CE} = V _{IH} or CE ₁ = V _{IL} , V _{OUT} = 0V to V _{CC}	-	10	_	5	μA
VoL	Output Low Voltage	$I_{OL} = +4mA$	_	0.4	_	0.4	V
Voh	Output High Voltage	lон = -4mA	2.4	_	2.4	_	V

NOTE:

3743 tbl 08

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range $^{(3,6,7)}$ (Vcc = 3.3V ± 0.3V)

Ор		pp.y toltage.			, -			-,			
						279X9 I Only		279X12 I Only		79X15 Only	
Symbol	Parameter	Test Condition	Versio	n	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
ICC	Dynamic Operating	CEL and CER= VIL, Outputs Disabled,	COM'L	S L	180 180	260 225	150 150	240 205	130 130	220 185	mA
	Current (Both Ports Active)	f = fMAX ⁽¹⁾	IND	S L		_		_			
ISB1	Standby Current (Both Ports - TTL	$\overline{CEL} = \overline{CER} = VIH$ $f = fMAX^{(1)}$	COM'L	S L	50 50	75 65	40 40	65 50	30 30	55 35	mA
	Level Inputs)	I = IMAX''	IND	S L		_		_			
ISB2	Standby Current (One Port - TTL	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH(5)	COM'L	S L	110 110	170 150	100 100	160 140	90 90	150 130	mA
	Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S L		_		_			
ISB3	Full Standby Current (Both Ports - CMOS	Both Ports \overline{CE} L and $\overline{CER} \ge VCC - 0.2V$, $VIN > VCC - 0.2V$ or	COM'L	S L	1.0 0.4	5 3	1.0 0.4	5 3	1.0 0.4	5 3	mA
	Level Inputs)	$VIN \ge VCC - 0.2V \text{ of } VIN \le 0.2V, f = 0^{(2)}$	IND	S L		_		_			
ISB4	Full Standby Current (One Port - CMOS	\overline{CE} "A" $\leq 0.2V$ and \overline{CE} "B" $\geq VCC - 0.2V^{(5)}$ VIN $> VCC - 0.2V$ or	COM'L	S L	100 100	160 140	90 90	150 130	80 80	140 120	mA
	Level Inputs)	$VIN \ge VCC - 0.2V$ of $VIN \le 0.2V$, Active Port, Outputs Disabled, $f = fMAX^{(1)}$	IND	S L		_		_		_	

3743 tbl 09

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right $\,$ port. Port "B" is the opposite from port "A".
- 4. Vcc = 3.3V, TA = 25°C for Typ, and are not production tested. lcc cc(f=0) = 90mA (Typ).
- 5. $\overline{CE}x = V_{IL} \text{ means } \overline{CE}_{0x} = V_{IL} \text{ and } CE_{1x} = V_{IH}$
 - $\overline{CE}x = VIH \text{ means } \overline{CE}0x = VIH \text{ or } CE1x = VIL$
 - $\overline{CE}x \le 0.2V$ means $\overline{CE}ox \le 0.2V$ and $CE_1x \ge Vcc 0.2V$
 - $\overline{\text{CE}}$ x \geq Vcc 0.2V means $\overline{\text{CE}}$ 0x \geq Vcc 0.2V or CE1x \leq 0.2V
 - 'X' represents "L" for left port or "R" for right port.
- 6. 'X' in part numbers indicate power rating (S or L).
- 7. Industrial temperature: for specific speeds, packages and powers contact your sales office.

^{1.} At $Vcc \le 2.0V$ input leakages are undefined.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2, and 3

7343 tbl 10

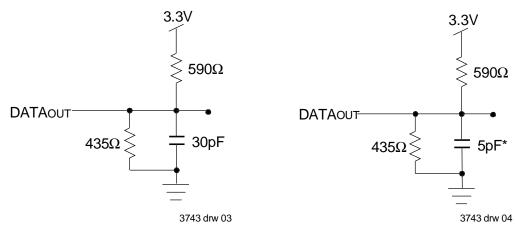


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tcklz, tckHz, tolz, and toHz). *Including scope and jig.

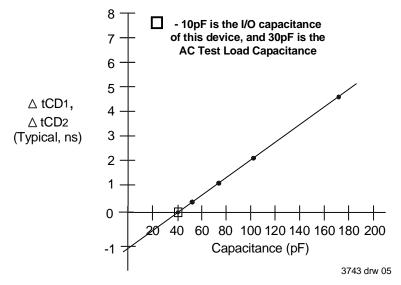


Figure 3. Typical Output Derating (Lumped Capacitive Load).

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(3,4,5)}$ (Vcc = 3.3V ± 0.3V, TA = 0°C to +70°C)

		70V9 Com'	279X9 I Only	70V92 Com	279X12 I Only	70V9: Com'	279X15 I Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	25		30	_	35	_	ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	15	_	20	_	25	_	ns
tcH1	Clock High Time (Flow-Through) ⁽²⁾	12	_	12	_	12	_	ns
tal1	Clock Low Time (Flow-Through) ⁽²⁾	12	_	12	_	12	_	ns
tch2	Clock High Time (Pipelined) ⁽²⁾	6	_	8	_	10	_	ns
tal2	Clock Low Time (Pipelined) ⁽²⁾	6		8	_	10	_	ns
tr	Clock Rise Time		3	—	3	_	3	ns
tF	Clock Fall Time		3	_	3	_	3	ns
tsa	Address Setup Time	4		4	_	4	_	ns
tha	Address Hold Time	1		1	_	1	_	ns
tsc	Chip Enable Setup Time	4		4	_	4	_	ns
tнc	Chip Enable Hold Time	1		1	_	1	_	ns
tsw	R/W Setup Time	4		4	_	4	_	ns
thw	R/W Hold Time	1		1	_	1	_	ns
tsd	Input Data Setup Time	4		4	_	4	_	ns
t HD	Input Data Hold Time	1	_	1	_	1	_	ns
tsad	ADS Setup Time	4		4	_	4	_	ns
thad	ADS Hold Time	1		1	_	1	_	ns
tscn	CNTEN Setup Time	4	_	4	_	4	_	ns
then	CNTEN Hold Time	1	_	1	_	1	_	ns
tsrst	CNTRST Setup Time	4		4	_	4	_	ns
thrst	CNTRST Hold Time	1		1	_	1	_	ns
tOE	Output Enable to Data Valid	_	12	_	12	_	15	ns
tolz	Output Enable to Output Low-Z ⁽¹⁾	2	_	2	_	2	_	ns
tонz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tcd1	Clock to Data Valid (Flow-Through) ⁽²⁾		20	_	25	_	30	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾		9	_	12	_	15	ns
toc	Data Output Hold After Clock High	2	_	2	_	2	_	ns
tckHz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2	_	2	_	2	_	ns
Port-to-Port I	Delay							-
tcwdd	Write Port Clock High to Read Data Delay		35	_	40	_	50	ns
tccs	Clock-to-Clock Setup Time	_	15	_	15	_	20	ns

NOTES:

^{1.} Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed characterization, but is not production tested.

by device

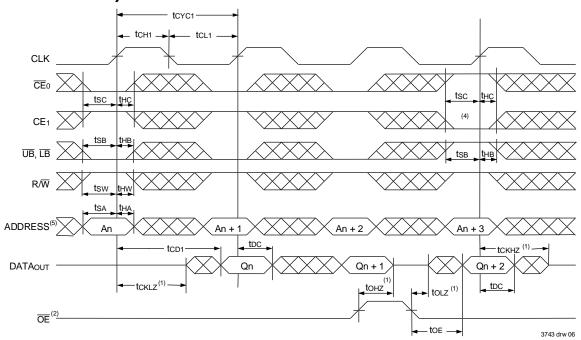
^{2.} The Pipelined output parameters (tcyc2, tcp2) apply to either or both left and right ports when FT/PIPE = VIH. Flow-through parameters (tcyc1, tcp1) apply when FT/PIPE = VIL for that port.

^{3.} All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE) and FT/PIPE. FT/PIPE should be treated as a DC signal, i.e. steady state during operation.

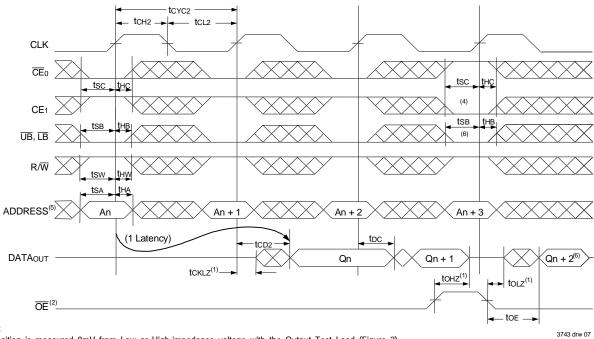
^{4. &#}x27;X' in part number indicates power rating (S or L).

^{5.} Industrial temperature: for specific speeds, packages and powers contact your sales office.

Timing Waveform of Read Cycle for Flow-through Output $(\overline{FT}/PIPE"x" = VIL)^{(3,7)}$

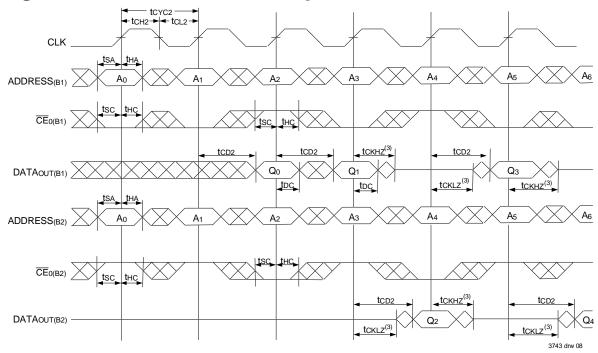


Timing Waveform of Read Cycle for Pipelined Output $(\overline{FT}/PIPE"x" = Vih)^{(3,7)}$

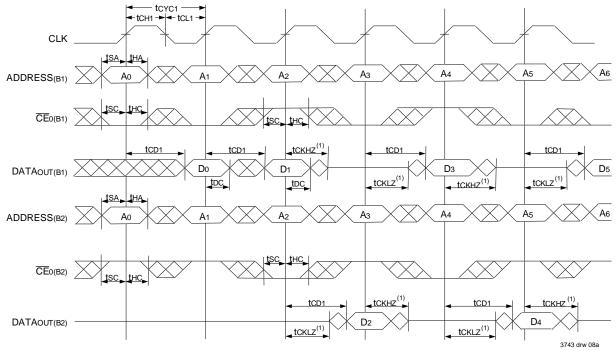


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- $\overline{\text{OE}}$ is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = VIL$, \overline{CNTEN} and $\overline{CNTRST} = VIH$.
- 4. The output is disabled (High-Impedance state) by $\overline{\text{CE}}_0 = \text{V}_{\text{IH}}$, $\overline{\text{CE}}_1 = \text{V}_{\text{IL}}$, $\overline{\text{UB}} = \text{V}_{\text{IH}}$, or $\overline{\text{LB}} = \text{V}_{\text{IH}}$ following the next rising edge of the clock. Refer to Truth Table 1.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 6. If UB or LB was HIGH, then the Upper Byte and/or Lower Byte of DATAouT for Qn + 2 would be disabled (High-Impedance state).
- 7. "x" denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read (1,2)



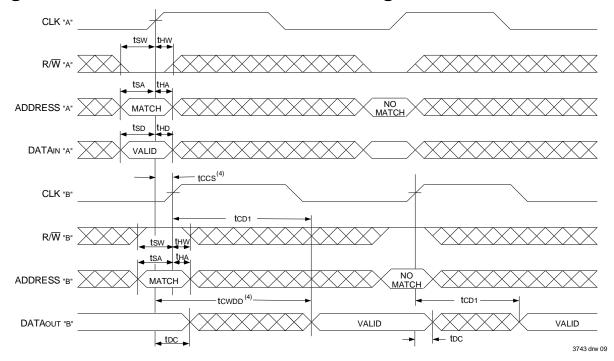
Timing Waveform of a Bank Select Flow-Through Read⁽⁶⁾



- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9279 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $\overline{ADS} = VIL$; \overline{CE}_1 , \overline{CNTEN} , and $\overline{CNTRST} = VIH$.
- 5. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 6. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpb.

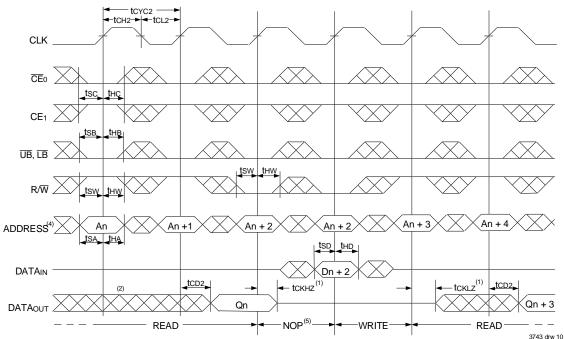
 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpb does not apply in this case.

Timing Waveform with Port-to-Port Flow-Through Read^(1,2,3,5)

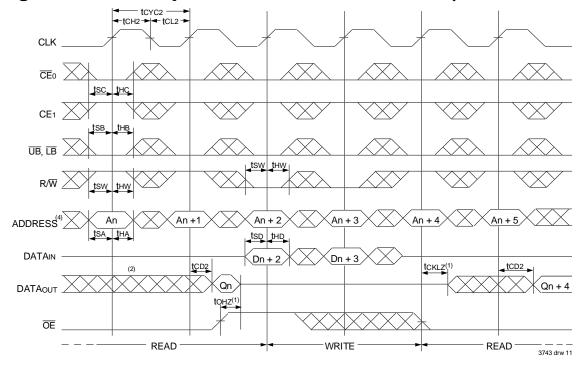


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and $\overline{ADS} = VIL$; CE_1 , \overline{CNTEN} , and $\overline{CNTRST} = VIH$.
- 3. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 4. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpb. If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpb does not apply in this case.
- 5. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{OE} = V_{IL}$)⁽³⁾

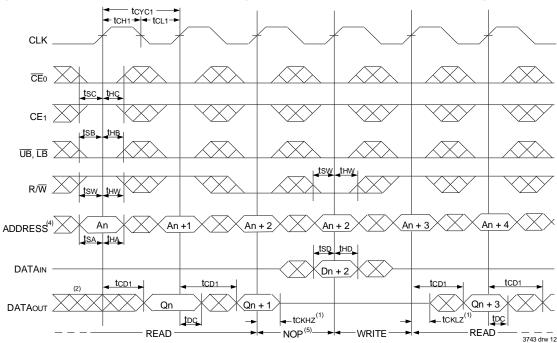


Timing Waveform of Pipelined Read-to-Write-to-Read (OE Controlled)(3)

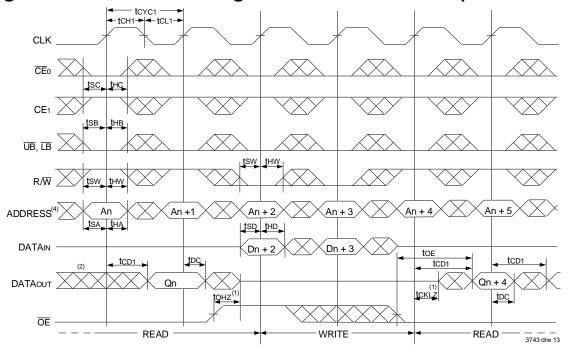


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; \overline{CE}_1 , \overline{CNTEN} , and \overline{CNTRST} = VIH.
- Addresses do not have to be accessed sequentially since ADS = Vil constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read $(\overline{OE} = V_{IL})^{(3)}$

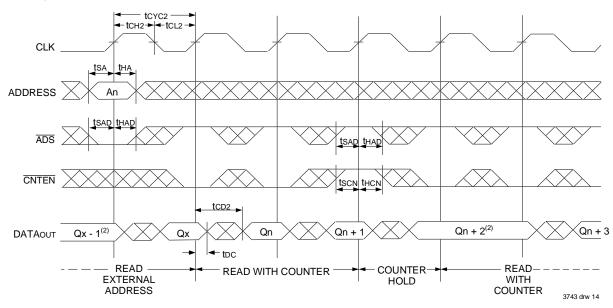


Timing Waveform of Flow-Through Read-to-Write-to-Read (OE Controlled)(3)

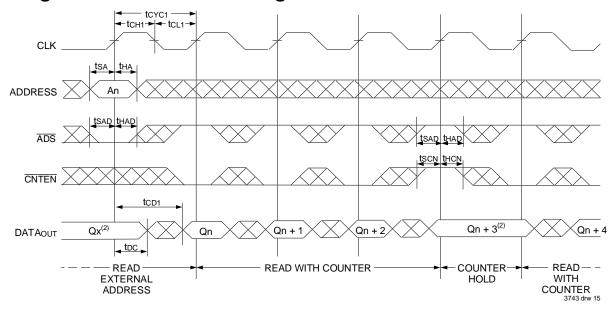


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; \overline{CE}_1 , \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 4. Addresses do not have to be accessed sequentially since \overline{ADS} = V_{IL} constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

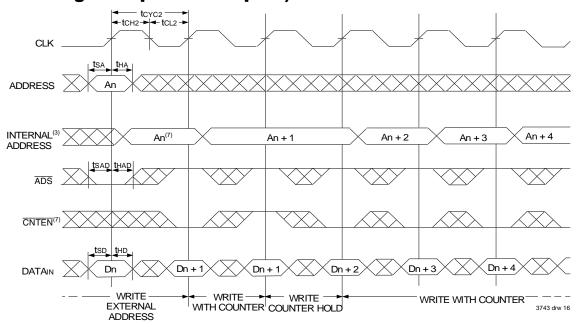


Timing Waveform of Flow-Through Read with Address Counter Advance $^{(1)}$

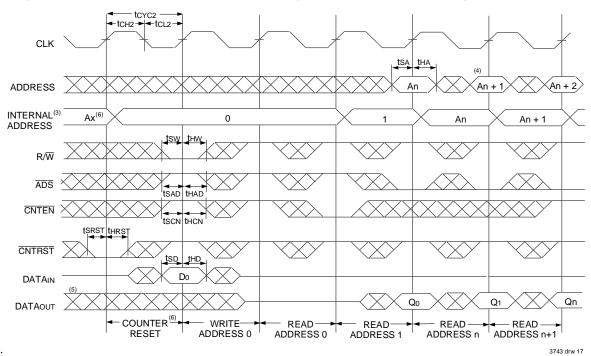


- 1. \overline{CE}_0 , \overline{OE} , \overline{UB} , and \overline{LB} = VIL; CE1, R/ \overline{W} , and \overline{CNTRST} = VIH.
- 2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)(2)



- 1. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{IL}$; CE_1 and $\overline{CNTRST} = V_{IH}$.
- 2. $\overline{CE_0}$, \overline{UB} , \overline{LB} = VIL; CE_1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{IL}$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle. ADDRo will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = V_{IL} advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance.
 The 'An +1'Address is written to during this cycle.

Functional Description

The IDT70V9279 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

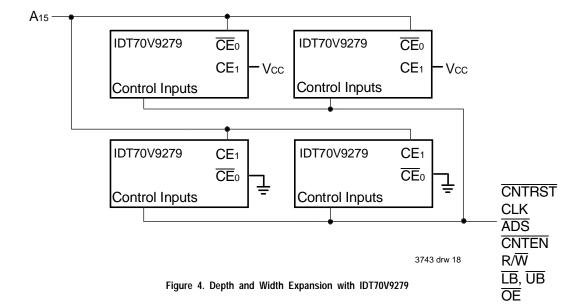
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to staff the operation of the address counters for fast interleaved memory applications.

A HIGH on $\overline{\text{CE}}$ 0 or a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V9279's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{\text{CE}}$ 0 LOW and CE1 HIGH to re-activate the outputs.

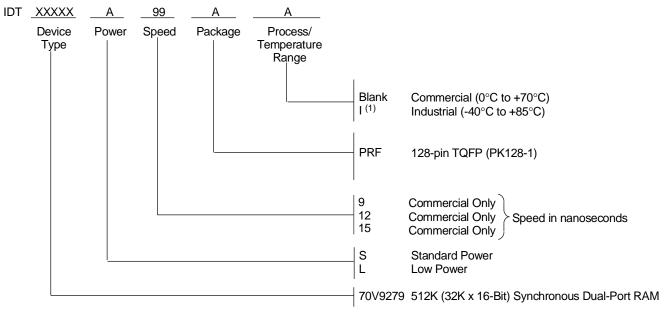
Depth and Width Expansion

The IDT70V9279 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70V9279 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 32-bit or wider applications.



Ordering Information



3743 drw 19

NOTE:

Industrial temperature range is available.
 For specific speeds, packages and powers contact your sales office.

Ordering Information for Flow-through Devices

Old Flow-through Part	New Combined Part
70V927S/L25	70V9279S/L12
70V927S/L30	70V9279S/L15

Datasheet Document History

1/12/99: Initiated datasheet document history

Converted to new format

Cosmetic and typographical corrections Added additional notes to pin configurations Page 14 Added Depth & Width Expansion section

6/15/99: Page 4 Deleted note 6 for Table II 9/29/99: Page 7 Corrected typo in heading

11/10/99: Replaced IDT logo

3/31/00: Combined Pipelined 70V9279 family and Flow-through 70V927 family offerings into one data sheet

Changed ±200mV in waveform notes to 0mV

Added corresponding part chart with ordering information

1/17/01: Page 4 Changed information in Truth Table II

Increased storage temperature parameters

Clarified TA parameter

Page 5 DC Electrical parameters-changed wording from "open" to "disabled"

Removed Preliminary status

